

Product Overview

NSD12416-Q1 is a 160mΩ 2 channel low-side switch with 48V clamp voltage for automotive applications. It's designed for driving resistive or inductive loads with one side connected to the battery. Internal 48V clamp circuit protects device from surge energy when fast demagnetization at turn-off.

With internal output current limitation, the device is protected in overload condition. Built-in thermal shutdown protects the chip from over-temperature and short-circuit. A thermal swing mechanism is built to limit dissipated power to decelerate power accumulation. Thermal shutdown, with automatic restart, allows the devices to recover normal operation as soon as a fault condition disappears.

An internal diagnose function is built to indicate any faults when thermal shutdown and open-drain conditions through an open-drain status output pin. This device operates in ambient temperatures from -40°C to 125°C.

Key Features

- AEC-Q100 qualified
- Drain current limitation: 2.5A
- 48V overvoltage clamp
- Thermal shutdown protection
- Thermal swing protection
- Fault diagnostic block
 - Thermal shutdown diagnosis
 - Open-drain diagnosis
- Very low standby current
- Very low electromagnetic susceptibility
- ESD protection

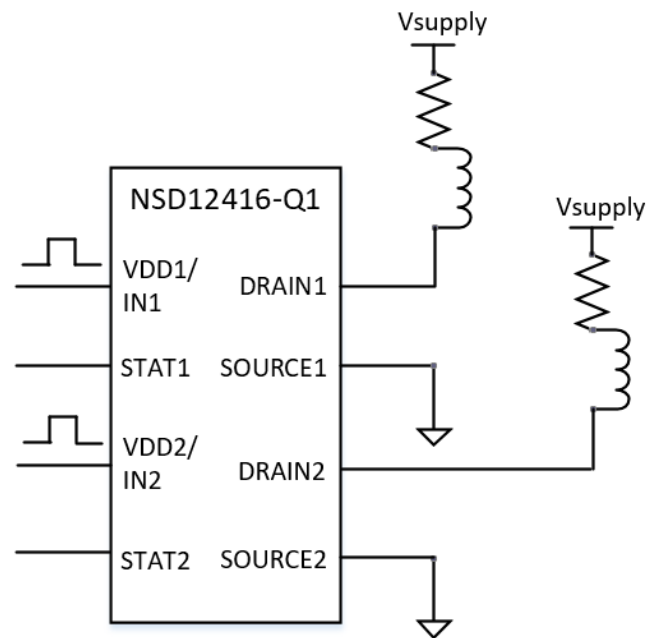
Applications

- Automotive Relays
- Solenoids
- Valves
- Lighting

Device Information

Part Number	Package	Body Size
NSD12416-Q1	SO-8	4.9mm x 3.9mm

Typical Application



Index

1. PIN CONFIGURATION AND FUNCTIONS	3
2. BLOCK DIAGRAM	3
3. ABSOLUTE MAXIMUM RATINGS.....	4
4. THERMAL INFORMATION.....	5
5. SPECIFICATIONS.....	5
5.1. ELECTRICAL CHARACTERISTICS.....	5
5.2. TYPICAL PERFORMANCE CHARACTERISTICS	6
5.2.1. <i>True table</i>	6
5.2.2. <i>Electrical characteristics curves</i>	7
6. PROTECTIONS	7
6.1. CURRENT LIMITATION	7
6.2. THERMAL SHUTDOWN AND THERMAL SWING	7
7. APPLICATION INFORMATION.....	7
7.1. MCU I/O PROTECTION	8
7.2. THE VALUE OF STATUS PULL UP RESISTOR	8
8. PACKAGE INFORMATION	10
9. ORDER INFORMATION.....	10
10. REVISION HISTORY	10

1. Pin Configuration and Functions

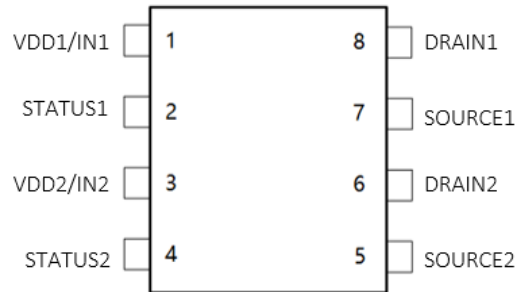
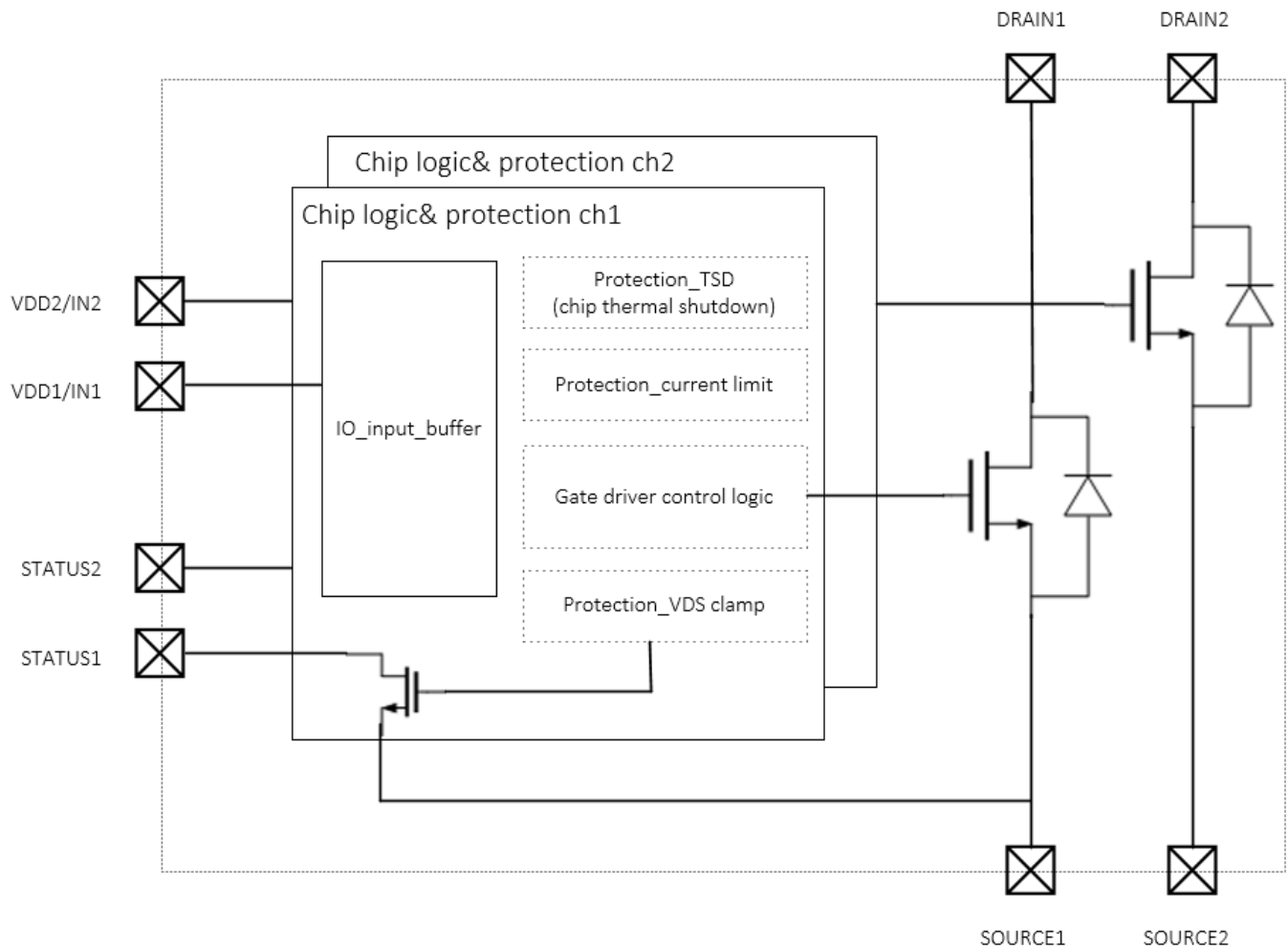


Table 1 SO-8 Pin Configuration and Description

PIN NO.	SYMBOL	FUNCTION
1,3	VDD1,2/IN1,2	Voltage controlled input pin with hysteresis, CMOS compatible. They controls output switch state
2,4	STATUS1,2	Open drain digital diagnostic pin
8,6	DRAIN1,2	PowerMOS drain
7,5	SOURCE1,2	PowerMOS source and ground reference for the control section

2. Block diagram



3. Absolute Maximum Ratings

Parameters	Symbol	Min	Typ	Max	Unit
Drain-to-Source Voltage	V_{DS}			Internally clamped	V
DC Drain Current	I_D			Thermal limited	A
Reverse DC drain current	$-I_D$			4	A
VDD Pin Current	I_{VDD}	-1		10	mA
INPUT Pin Current	I_{IN}	-1		10	mA
STATUS Pin Current	I_{STAT}	-1		10	mA
Junction Temperature	T_J	-40		150	°C

Parameters	Symbol	Min	Typ	Max	Unit
Storage Temperature	T_{stg}	-55		150	°C
Electrostatic discharge, Human-body model	HBM	-4000		4000	V
Electrostatic discharge, Charged-device model	CDM	-750		750	V

4. Thermal Information

Parameters	Symbol	SO-8	SOT223	Unit
IC Junction-to-ambient Thermal Resistance	θ_{JA}	99	145	°C/W

5. Specifications

5.1. Electrical Characteristics

(VDD = VIN = 4.5 V to 5.5 V, Tj = -40°C to 150°C. Unless otherwise noted.)

Parameters	Symbol	Min	Typ	Max	Unit	Comments
Power MOSFET						
ON-state resistance	R_{ON}			160	mΩ	ID = 1 A; Tj = 25°C; VDD = VIN = 5 V
				320	mΩ	ID = 1 A; Tj = 150°C; VDD = VIN = 5 V
Drain-source clamp voltage	V_{CLAMP}	46	48	56	V	VIN = 0V, ID = 1A
Drain-source clamp threshold voltage	V_{CLTH}	40			V	VIN = 0V, ID = 2 mA
OFF-state output current	I_{DSS}	0		3	μA	VIN = 0 V; VDS = 13 V; Tj = 25°C
		0		5	μA	VIN = 0 V; VDS = 13 V; Tj = 125°C
Bode diode forward voltage	V_{BD}		0.8		V	ID = 1A; VIN = 0 V
Input section						
Supply current from input pin	I_{ISS}		30	65		ON-state; VDD=VIN = 5 V; VDS = 0 V
Input clamp voltage	V_{ICL}	5.5		7	V	IICL = 1 mA
			-0.7			IICL = -1 mA
Input threshold voltage	V_{INTH}	1		3.5	V	VDS = VIN; ID = 1 mA
Status indicator						
Status low output voltage	V_{STAT}			0.5	V	I _{STAT} = 1 mA

Parameters	Symbol	Min	Typ	Max	Unit	Comments
Status leakage current	I_{LSTAT}			10	μA	$V_{STAT} = 5\text{ V}$
Status pin input capacitance	C_{STAT}			100	pF	$V_{STAT} = 5\text{ V}$
Status clamp voltage	V_{STCT}	5.5		7	V	$I_{STAT} = 1\text{ mA}$
			-0.7			$I_{STAT} = -1\text{ mA}$
Switching characteristics (See Figure 6 for Switching timing characteristics)						
Turn-on delay time	$t_{d(ON)}$		8		μs	$R_L = 13\ \Omega, V_{CC} = 13\text{ V}$
Turn-off delay time	$t_{d(OFF)}$		8		μs	$R_L = 13\ \Omega, V_{CC} = 13\text{ V}$
Rise time	t_r		10		μs	$R_L = 13\ \Omega, V_{CC} = 13\text{ V}$
Fall time	t_f		10		μs	$R_L = 13\ \Omega, V_{CC} = 13\text{ V}$
Switching energy losses at turn-on	W_{ON}		TBD		μJ	$R_L = 13\ \Omega, V_{CC} = 13\text{ V}$
Switching energy losses at turn-off	W_{OFF}		TBD		μJ	$R_L = 13\ \Omega, V_{CC} = 13\text{ V}$
Protection and diagnostics						
DC short-circuit current	I_{limH}	1.8	2.5	3	A	$V_{DS} = 13\text{ V}, V_S = V_{IN} = 5\text{ V}$
Shutdown temperature	TTSD	150	175	200	$^{\circ}\text{C}$	
Reset temperature	TR	$T_{RS} + 1$	$T_{RS} + 5$		$^{\circ}\text{C}$	
Thermal reset of STATUS	TRS	135			$^{\circ}\text{C}$	
Thermal hysteresis (TTSD - TR)	THYST		7		$^{\circ}\text{C}$	
Dynamic temperature	ΔT_j		40		K	$T_j = -40^{\circ}\text{C}, V_{CC} = 13\text{ V}$
Dynamic temperature hysteresis	$\Delta T_j(\text{HYS})$		15		K	

5.2. Typical Performance Characteristics

5.2.1. True table

Conditions	Input	Drain	Status
Normal operation	L	H	H
	H	L	H
Current limitation	L	H	H
	H	X	H
Over-temperature limitation	L	H	H
	H	H	L
VDD under-voltage	L	H	X

<i>Conditions</i>	<i>Input</i>	<i>Drain</i>	<i>Status</i>
	H	H	X
Open-drain detection	L	L	L
	H	L	H

5.2.2. Electrical characteristics curves

6. Protections

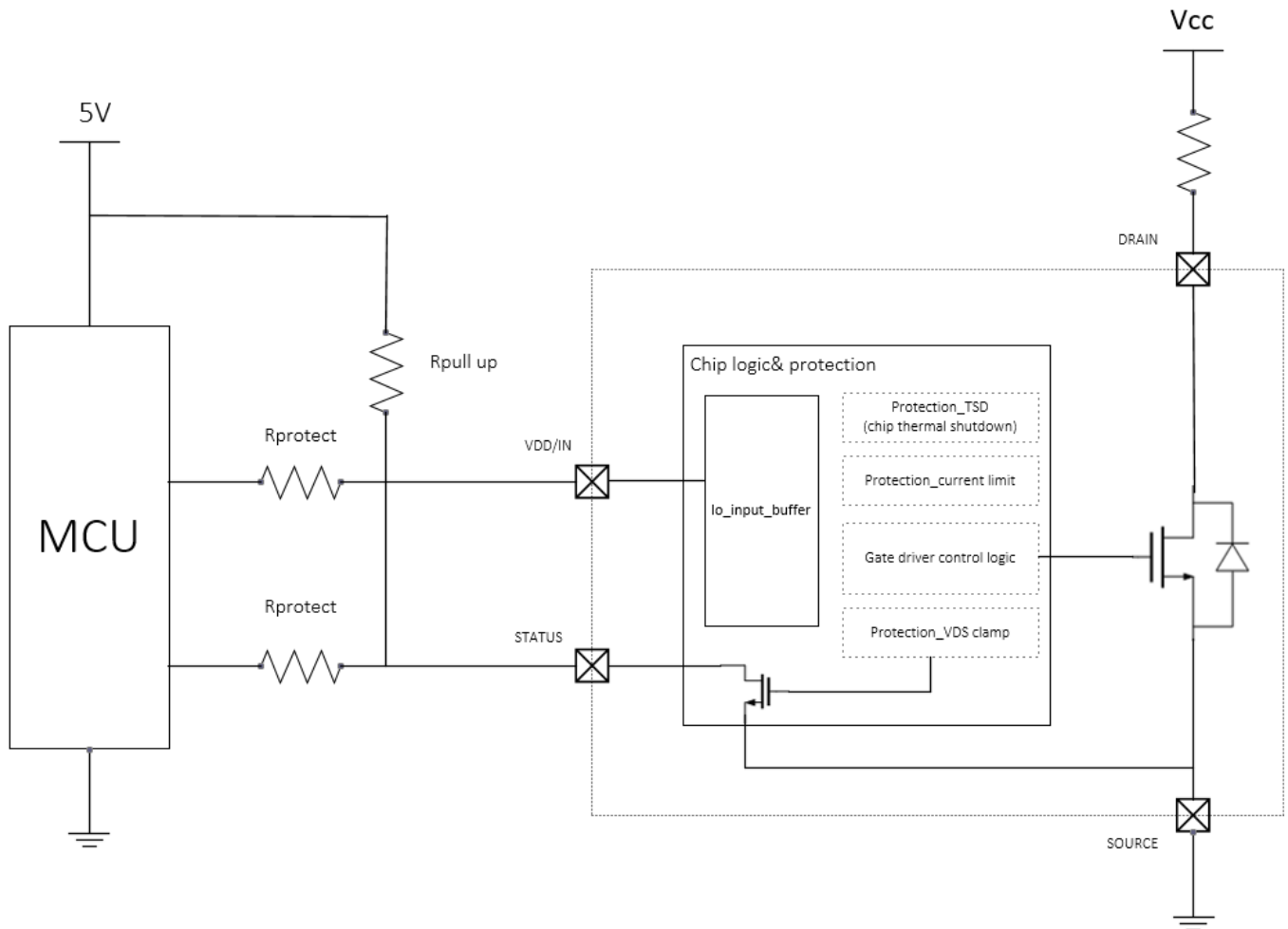
6.1. Current limitation

NSD12416-Q1 has current limitation to protect the silicon and bonding wire in case of overload or short circuit to ground.

6.2. Thermal shutdown and thermal swing

This device has both absolute and dynamic temperature protection. There are two thermal sensors on the controller and the MOSFET, the one on the MOSFET is the hottest and the one on the controller is the coldest. The absolute temperature protection is to shutdown the MOSFET when the hottest junction temperature exceeds the T_{TSD} , and the dynamic temperature protection is also to shutdown the MOSFET when the temperature difference between the hottest and the coldest exceeds ΔT_j .

7. Application Information



7.1. MCU I/O protection

NSD12416 has Zener diodes inside for ESD protection and the intrinsic NPN parasitic bipolar, so that resistors for protection are necessary in series with the digital inputs to limit the current to protect MCU I/Os during transient and reverse battery conditions.

The value of resistors for protection can be calculated by the formula as shown below:

$$\frac{V_{ICL}}{I_{latchup}} \leq R_{prot} \leq \frac{V_{MCU_OUT} - V_{IH}}{I_{IH\ max}}$$

Where V_{ICL} is reverse clamp voltage of NSD12416, $I_{latchup}$ is the MCU I/O latch up current, V_{MCU_OUT} is the output voltage of MCU I/O, V_{IH} is the High-level input voltage of NSD12416, I_{IH} is the high level input current.

Let:

$I_{latchup} \geq 20\text{mA}$; $V_{MCU_OUT} \geq 4.5\text{V}$, so $35\Omega \leq R_{prot} \leq 100\text{k}\Omega$, the recommended value is $1\text{k}\Omega$.

7.2. The value of STATUS pull up resistor

Because the STATUS pin is open drain output, a pull up resistor is needed to fix the high voltage during normal operation. When the fault occurs, the voltage level of STATUS is pulled down by the internal MOSFET on. The value of pull up resistor can be calculated by the formula as shown below:

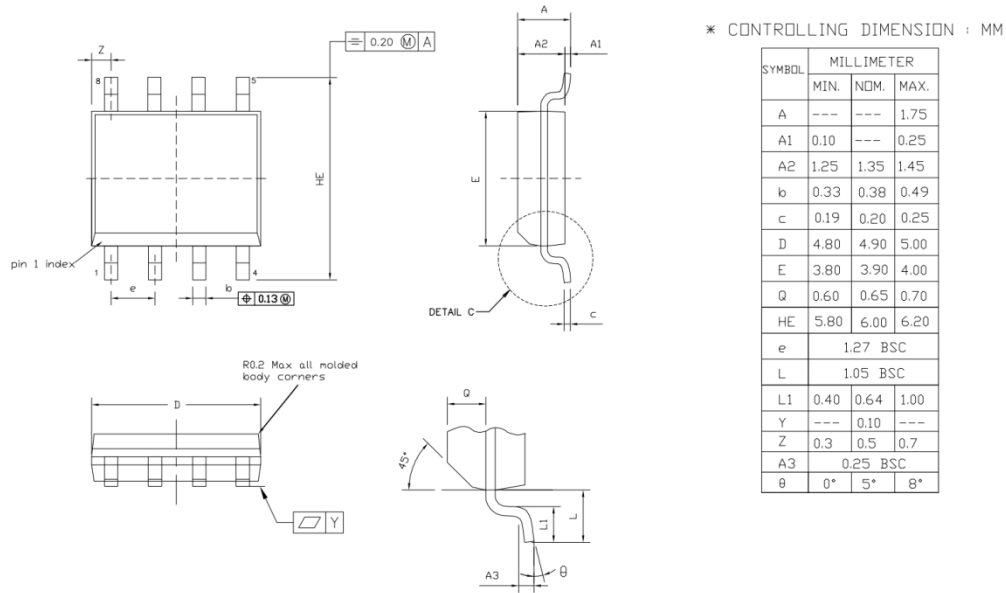
$$\left(\frac{V_{pull-up}}{V_{OL}} - 1\right) \bullet R_{on} < R_{pull-up} < \frac{V_{pull-up} - V_{OH}}{I_{leak}}$$

Where V_{pullup} is the minimum of pull-up supply, V_{OL} is the maximum of MCU logic low, R_{on} is the on resistance of the MOSFET of STATUS pin, V_{OH} is the minimum of MCU logic high, I_{leak} is the maximum leakage current of STATUS pin.

Let:

$V_{pullup} = 4.5V$; $R_{on} = V_{STAT}/I_{STAT} = 500\Omega$, $V_{OL} = 0.9V$; $V_{OH} = 2.1V$; $I_{leak} = 10\mu A$, so $2k\Omega \leq R_{pullup} \leq 240k\Omega$.

8. Package Information



9. Order Information

Part Number	Package
NSD12416-QSPR	SO-8

10. Revision history

Revision	Description	Date
0V1	Initial version	2022/07
0V2	Second version	2022/9/30
0V3	Third version	2022/11/28